JUN 0 1 2004 2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Robert Chau et al.

Serial No.: 10/618,226

Filed:

July 11, 2003

For:

A METHOD FOR MAKING A SEMICONDUCTOR

DEVICE HAVING A

HIGH-K GATE DIELECTRIC

Which is a Continuation of Application:

Serial No.: 10/082,530

Filed:

February 22, 2002

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 Examiner:

J. Chen

Art Unit:

2813

Attorney Docket No: P12759C

Examiner: C. Lee

Art Unit: 2825

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97 (c) WITH CERTIFICATION UNDER 37 C.F.R. § 1.97 (e)(2)

Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, Applicant(s) wish to call the following documents (copies enclosed) to the attention of the Examiner. The documents were cited in the International Search Report (copy enclosed) for International Application No. PCT/US 03/35955. That international application is not a counterpart foreign application to the pending application.

A Form PTO-1449 listing these documents is enclosed.

Citation of the above documents shall not be construed as:

- 1 an admission that the documents are necessarily prior art with respect to the instant invention;
- 2 a representation that a search has been made, other than as described above; or
- 3 an admission that the information cited herein is, or is considered to be, material to patentability as defined in §1.56(b).

The undersigned hereby certifies in accordance with § 1.97(e)(2) that no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in § 1.56(c) more than three months prior to the filing of the statement.

Respectfully submitted,

Dated: May 26, 2004

Mark V. Seeley

Reg. No. 32,299

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FIRST CLASS CERTIFICATE OF MAILING

(37 C.F.R. § 1.8(a))

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail with sufficient postage in an envelop addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

Date of Deposit Seeley

Name of Person Mailing Correspondence

May 26 26

Form			•		ty Docket	N C	P12759C	Serial No.:	10/618	3,226		
List of Patents and Publications atement (Use several sheets if necessary)							Applicant:		Robert Chau et al.			
							Filing Date: July 11, 2003			1, 2003	····	
REFERENCE DESIGNATION						U.S. PATENT DOCUMENTS						
Examiner Initials			Document No.						Class	Sub- Class	Filing date if appropriate	
			AA	6,020,024			et al.		427	248.1		
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